

Shin-Ichi Kanemaru

List of Publications by Year in descending order

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141
papers

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279487

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142
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142
times ranked

1028
citing authors

#	ARTICLE	IF	CITATIONS
1	The efficacy of a novel collagen-gelatin scaffold with basic fibroblast growth factor for the treatment of vocal fold scar. <i>Journal of Tissue Engineering and Regenerative Medicine</i> , 2017, 11, 1598-1609.	1.3	26
2	Biocompatibility and Efficacy of Collagen/Gelatin Sponge Scaffold With Sustained Release of Basic Fibroblast Growth Factor on Vocal Fold Fibroblasts in 3-Dimensional Culture. <i>Annals of Otolaryngology, Rhinology and Laryngology</i> , 2015, 124, 116-125.	0.6	23
3	Regenerative Treatment for Soft Tissue Defects of the External Auditory Meatus. <i>Otology and Neurotology</i> , 2014, 35, 442-448.	0.7	5
4	Densification of spin-on-glass (SOG) film by RF plasma treatment. <i>IOP Conference Series: Materials Science and Engineering</i> , 2011, 18, 032007.	0.3	0
5	Ion induced bending (IIB) phenomenon for 3-D structure fabrication. <i>Surface and Coatings Technology</i> , 2011, 206, 775-780.	2.2	1
6	Integration of thin film transistors and vertical thin film field emitter arrays using ion-induced bending. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, 032205.	0.6	2
7	Enhancement of ion-induced bending phenomenon using a double-layered film for field emitter array fabrication. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, C2C1-C2C4.	0.6	2
8	Characteristics of Ion-Induced Bending Phenomenon. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 056501.	0.8	15
9	10.2: Integration of TFT and VTF-FEA using ion-induced bending. , 2010, , .		0
10	Development of a CdTe x-ray imaging device driven by a vertical thin film field emission array. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, C2D22-C2D25.	0.6	1
11	Fabrication of a Field Emitter Array with a Built-in Einzel Lens. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 06FK02.	0.8	26
12	CdTe x-ray image sensor using a field emitter array. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 725-728.	1.3	8
13	Emission and focusing characteristics of volcano-structured double-gated field emitter arrays. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 701-704.	1.3	21
14	Design and fabrication of an ultrahigh-luminance field-emission display. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 740.	1.3	2
15	Room-temperature crystallization of amorphous films by RF plasma treatment. <i>Thin Solid Films</i> , 2009, 517, 3092-3095.	0.8	20
16	Determination of the best conditions of scaffolds for tissue engineered canine skull regeneration. <i>Laryngoscope</i> , 2009, 119, S257.	1.1	0
17	Development of Thin-Film Bending Technique Induced by Ion-Beam Irradiation. <i>Applied Physics Express</i> , 2009, 2, 066501.	1.1	14
18	Fabrication of Volcano-Structured Double-Gate Field Emitter Array by Etch-Back Technique. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 5252-5255.	0.8	22

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19	Field emitter array with a memory function for ultrahigh luminance field emission display. <i>Journal of Vacuum Science & Technology B</i> , 2007, 25, 464.	1.3	11
20	Stabilization technique for columella using trimmed autologous temporal fascia in type III and IV tympanoplasty â€“ muffler method. <i>Acta Oto-Laryngologica</i> , 2007, 127, 44-46.	0.3	3
21	A case report of myasthenia gravis localized to the larynx. <i>Auris Nasus Larynx</i> , 2007, 34, 401-403.	0.5	9
22	A case of floppy epiglottis in adult: A simple surgical remedy. <i>Auris Nasus Larynx</i> , 2007, 34, 409-411.	0.5	23
23	5-Fluorouracil Ointment for the Treatment of Otitis Media With Effusion. <i>Laryngoscope</i> , 2007, 117, 215-219.	1.1	5
24	A regenerative approach for partial tracheal defects, an in vivo canine model. <i>Inflammation and Regeneration</i> , 2007, 27, 570-574.	1.5	3
25	HfC field emitter array controlled by built-in poly-Si thin film transistor. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 936.	1.3	18
26	Parameter dispersion characterization for arrays of HfC-coated emitters on poly-Si substrate. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 1045.	1.3	4
27	Doping integrity diagnostics of planar transistor channel structures by scanning nonlinear dielectric microscopy. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 237.	1.3	0
28	Work function controllability of metal gates made by interdiffusing metal stacks with low and high work functions. <i>Microelectronic Engineering</i> , 2005, 80, 284-287.	1.1	12
29	Silicon field emission array as novel charge neutralization device for high current ion implanter. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 237, 390-394.	0.6	12
30	Regeneration of Mastoid Air Cells in Clinical Applications by In Situ Tissue Engineering. <i>Laryngoscope</i> , 2005, 115, 253-258.	1.1	25
31	Demonstration, Analysis, and Device Design Considerations for Independent DG MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2005, 52, 2046-2053.	1.6	115
32	Emission Statistics for HfC Emitter Arrays after Residual Gas Exposure. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 5959-5963.	0.8	2
33	Fabrication of HfC-Coated Si Field Emitter Arrays with Built-in Poly-Si Thin-Film Transistor. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 5740-5743.	0.8	5
34	Scanning tunneling microscopy observations of hafnium carbide thin films as a field emission material. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 741.	1.6	7
35	Ring-shaped images as a result of nonuniform field emission from capped carbon nanotubes. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 649.	1.6	10
36	Emission statistics for Si and HfC emitter arrays after residual gas exposure. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 707.	1.6	73

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37	Work function uniformity of Al–Ni alloys obtained by scanning Maxwell-stress microscopy as an effective tool for evaluating metal transistor gates. <i>Applied Physics Letters</i> , 2005, 86, 094104.	1.5	9
38	Destiny of Autologous Bone Marrow–Derived Stromal Cells Implanted in the Vocal Fold. <i>Annals of Otolaryngology, Rhinology and Laryngology</i> , 2005, 114, 907-912.	0.6	78
39	Fabrication and characterization of vertical-type, self-aligned asymmetric double-gate metal-oxide-semiconductor field-effect-transistors. <i>Applied Physics Letters</i> , 2005, 86, 123512.	1.5	9
40	P-Channel Vertical Double-Gate MOSFET Fabricated by Utilizing Ion-Bombardment-Retarded Etching Process. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 2156-2159.	0.8	2
41	Fabrication of Polycrystalline Silicon Field Emitter Arrays with Hafnium Carbide Coating for Thin-Film-Transistor Controlled Field Emission Displays. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 3919-3922.	0.8	15
42	Characterization of enhanced field emission from HfC-coated Si emitter arrays through parameter extraction. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004, 22, 1227.	1.6	15
43	Modeling of Optimized Field Emission Nanotriodes with Aligned Carbon Nanotubes of Variable Heights. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 485-491.	0.8	18
44	Modeling of Focused Carbon Nanotube Array Emitters for Field-Emission Displays. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 3328-3334.	0.8	6
45	Tissue engineering for the regeneration of the mastoid air cells: A preliminary in vitro study. <i>Acta Oto-Laryngologica</i> , 2004, 124, 75-79.	0.3	7
46	Regeneration of mastoid air cells: Clinical applications. <i>Acta Oto-Laryngologica</i> , 2004, 124, 80-84.	0.3	9
47	Ultrathin Channel Vertical DG MOSFET Fabricated by Using Ion-Bombardment-Retarded Etching. <i>IEEE Transactions on Electron Devices</i> , 2004, 51, 2078-2085.	1.6	50
48	Diagnostics of doping integrity in n+/p/n+ transistor-channel structure by scanning nonlinear dielectric microscopy. <i>Applied Physics Letters</i> , 2004, 84, 3169-3171.	1.5	6
49	Doping diagnosis by evaluation of the surface Fermi level using scanning Maxwell-stress microscopy. <i>Applied Physics Letters</i> , 2003, 82, 2166-2168.	1.5	3
50	Modeling of field emission nanotriodes with carbon nanotube emitters. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 366.	1.6	27
51	Model parameter extraction for nonlinear Fowler–Nordheim field emission data. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 1550.	1.6	14
52	Programmable Conductivity of Silicon Nanowires with Side Gates by Surface Charging. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 2422-2425.	0.8	1
53	Fabrication of ultrathin Si Channel Wall For Vertical Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor (DG MOSFET) by Using Ion-Bombardment-Retarded Etching (IBRE). <i>Japanese Journal of Applied Physics</i> , 2003, 42, 1916-1918.	0.8	13
54	Novel Process for Vertical Double-Gate (DG) Metal-Oxide-Semiconductor Field-Effect-Transistor (MOSFET) Fabrication. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 4138-4141.	0.8	7

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55	Silicon nanowire with programmable conductivity analyzed by scanning Maxwell-stress microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 664.	1.6	3
56	Metal-oxide-semiconductor field-effect transistor-structured Si field emitter array with a built-in ring gate lens. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 495.	1.6	3
57	Fabrication and characterization of HfC coated Si field emitter arrays. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 1589.	1.6	51
58	Emission uniformity improvement of Si field emitter arrays by surface modification. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 1581.	1.6	17
59	Current Status of Vacuum Microelectronics. <i>IEEJ Transactions on Fundamentals and Materials</i> , 2003, 123, 425-428.	0.2	1
60	Mechanism of Tungsten Plug Corrosion during Chemical Stripping Process: Scanning Maxwell-Stress Microscopy and Electrochemical Potentiometry Studies. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5108-5112.	0.8	4
61	Fabrication of Si field emitter arrays integrated with metal-oxide-semiconductor field-effect transistor driving circuits. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 2309.	1.6	24
62	Dual-Gate Electron Emission Structure with Nanotube-on-Emitter for X-Ray Generation. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5551-5556.	0.8	8
63	Close Observation of the Geometrical Features of an Ultranarrow Silicon Nanowire Device. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 4419-4422.	0.8	2
64	Oscillator Ionization Vacuum Gauge with Field Emitters. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5945-5950.	0.8	1
65	Damageless vacuum sealing of Si field emitters with CHF ₃ plasma treatment. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 920.	1.6	13
66	Emission-uniformity improvement and work-function reduction of Si emitter tips by ethylene gas exposure. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1911.	1.6	9
67	Charging Damage of Silicon-on-Insulator (SOI) Wafer Determined by Scanning Maxwell-Stress Microscopy. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 2907-2910.	0.8	2
68	Electron Motion Three-Dimensional Confinement for Microelectronic Vacuum Gauges with Field Emitters. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 2165-2172.	0.8	2
69	Fabrication of a vacuum-sealed magnetic sensor with a Si field emitter tip. <i>Journal of Micromechanics and Microengineering</i> , 2001, 11, 81-83.	1.5	8
70	Characterization of electrical conduction in silicon nanowire by scanning Maxwell-stress microscopy. <i>Applied Physics Letters</i> , 2001, 78, 2560-2562.	1.5	20
71	Single electron memory characteristic of silicon nanodot nanowire transistor. <i>Electronics Letters</i> , 2000, 36, 1322.	0.5	11
72	Highly suppressed short-channel effects in ultrathin SOI n-MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2000, 47, 354-359.	1.6	103

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73	Individual tip evaluation in Si field emitter arrays by electrostatic lens projector. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 952.	1.6	11
74	CHF3 Plasma Treatment of Si Field Emitter Arrays For No Damage Vacuum Packaging. Japanese Journal of Applied Physics, 2000, 39, L755-L756.	0.8	7
75	Effects of conduction type on field-electron emission from single Si emitter tips with extraction gate. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1111.	1.6	14
76	Fabrication of 40 μ m Gate Length Ultrathin n-MOSFETs Using Epitaxial Layer Transfer SOI Wafers. Japanese Journal of Applied Physics, 1999, 38, 2492-2495.	0.8	3
77	Emission Characteristics of Amorphous Silicon Field Emitter Arrays Sealed in a Vacuum Package. Japanese Journal of Applied Physics, 1999, 38, 7213-7216.	0.8	1
78	Electrical Characteristics of Air-Bridge-Structured Silicon Nanowire Fabricated by Micromachining a Silicon-on-Insulator Substrate. Japanese Journal of Applied Physics, 1999, 38, 7237-7240.	0.8	9
79	Plane-view observation technique of silicon nanowires by transmission electron microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1897.	1.6	5
80	Fabrication technology of ultrafine SiO ₂ masks and Si nanowires using oxidation of vertical sidewalls of a poly-Si layer. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 77.	1.6	4
81	Low-voltage operation from the tower structure metal-oxide-semiconductor field-effect transistor Si field emitter. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 588.	1.6	15
82	Air-bridge-structured silicon nanowire and anomalous conductivity. Applied Physics Letters, 1999, 75, 3986-3988.	1.5	39
83	Stable emission from a MOSFET-structured emitter tip in poor vacuum. Applied Surface Science, 1999, 146, 198-202.	3.1	23
84	Fabrication and characterization of a nanogap edge emitter with a silicon-on-insulator wafer. Applied Surface Science, 1999, 146, 203-208.	3.1	19
85	Improvement of electron emission characteristics of Si field emitter arrays by surface modification. Applied Surface Science, 1999, 146, 172-176.	3.1	4
86	A field emitter array monolithically integrated with a thin-film transistor on glass for display applications. Applied Surface Science, 1999, 146, 187-192.	3.1	8
87	Optimization of transistor structure for transistor-stabilized field emitter arrays. IEEE Transactions on Electron Devices, 1999, 46, 2261-2264.	1.6	9
88	Fabrication of a New Field Emitter Array with a Built-in Thin-Film Transistor on Glass. Japanese Journal of Applied Physics, 1998, 37, 7134-7137.	0.8	5
89	Fabrication of a Nanometer-Scale Si-Wire by Micromachining of a Silicon-on-Insulator Substrate. Japanese Journal of Applied Physics, 1998, 37, 7182-7185.	0.8	19
90	Suppressed threshold voltage roll-off characteristic of 40 nm gate length ultrathin SOI MOSFET. Electronics Letters, 1998, 34, 2069.	0.5	12

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91	Three-dimensional vacuum magnetic sensor with a Si emitter tip. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1233.	1.6	13
92	A field emitter array with an amorphous silicon thin-film transistor on glass. Applied Physics Letters, 1998, 73, 1301-1303.	1.5	8
93	Fabrication of a Three-Dimensional Vacuum Magnetic Sensor with a Si Tip. Japanese Journal of Applied Physics, 1997, 36, 7754-7756.	0.8	7
94	Fabrication of Metal-Oxide-Semiconductor Field-Effect-Transistor-Structured Silicon Field Emitters with a Polysilicon Dual Gate. Japanese Journal of Applied Physics, 1997, 36, 7736-7740.	0.8	17
95	Control of emission currents from silicon field emitter arrays using a built-in MOSFET. Applied Surface Science, 1997, 111, 218-223.	3.1	46
96	Beam focusing characteristics of silicon microtips with an in-plane lens. IEEE Transactions on Electron Devices, 1997, 44, 498-502.	1.6	30
97	Amorphous-silicon-on-glass field emitter arrays. IEEE Electron Device Letters, 1996, 17, 261-263.	2.2	6
98	Fabrication of a New Si Field Emitter Tip with Metal-Oxide-Semiconductor Field-Effect Transistor (MOSFET) Structure. Japanese Journal of Applied Physics, 1996, 35, 6637-6640.	0.8	34
99	Ultrastable emission from a metal-oxide-semiconductor field-effect transistor-structured Si emitter tip. Applied Physics Letters, 1996, 69, 1577-1578.	1.5	49
100	A New Metal-Oxide-Semiconductor Field-Effect-Transistor-Structured Si Field Emitter Tip. Japanese Journal of Applied Physics, 1996, 35, L861-L863.	0.8	31
101	Fabrication of Field Emitter Arrays with Hydrogenated Amorphous Silicon on Glass. Japanese Journal of Applied Physics, 1996, 35, 6620-6622.	0.8	4
102	Fabrication of Si Field Emitter Tip for a Three-Dimensional Vacuum Magnetic Sensor. Japanese Journal of Applied Physics, 1996, 35, 6629-6631.	0.8	17
103	Electron-beam characteristics of double-gated Si field emitter arrays. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1902.	1.6	23
104	Emission current saturation of the p-type silicon gated field emitter array. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 3357.	1.6	24
105	Control of emission characteristics of silicon field emitter arrays by an ion implantation technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1885.	1.6	37
106	Microscopic characterization of field emitter array structure and work function by scanning Maxwell-stress microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2105.	1.6	16
107	Fabrication of Silicon Field Emitter Arrays Integrated with Beam Focusing Lens. Japanese Journal of Applied Physics, 1996, 35, 6626-6628.	0.8	30
108	Fabrication of double-gated Si field emitter arrays for focused electron beam generation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1968.	1.6	99

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109	Fabrication of an ultrasharp and high-aspect-ratio microprobe with a silicon-on-insulator wafer for scanning force microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 331.	1.6	21
110	Emission Characteristics of Ion-Implanted Silicon Emitter Tips. Japanese Journal of Applied Physics, 1995, 34, 6907-6911.	0.8	29
111	Nanoscale Evaluation of Structure and Surface Potential of Gated Field Emitters by Scanning Maxwell-Stress Microscope. Japanese Journal of Applied Physics, 1995, 34, 6912.	0.8	4
112	Fabrication of Silicon Field Emitter Arrays with 0.1- μ m-Diameter Gate by Focused Ion Beam Lithography. Japanese Journal of Applied Physics, 1995, 34, 6932-6934.	0.8	5
113	Fabrication of Petal-Shaped Vertical Field Emitter Arrays. Japanese Journal of Applied Physics, 1995, 34, 6916-6921.	0.8	3
114	Feasibility of Vacuum Microelectronics Voltage Comparator. Japanese Journal of Applied Physics, 1995, 34, 6219-6221.	0.8	1
115	Nanoscale Evaluation of Structure and Surface Potential of Gated Field Emitters by Scanning Maxwell-Stress Microscope. Japanese Journal of Applied Physics, 1995, 34, 6912-6915.	0.8	3
116	Fabrication and Characterization of Cross-Edge-Structured Vertical Field Emitter Arrays. Japanese Journal of Applied Physics, 1994, 33, 7171-7175.	0.8	2
117	Vacuum Microtriode with Comb-Shaped Lateral Field-Emitter Array. Japanese Journal of Applied Physics, 1993, 32, L809-L812.	0.8	9
118	Fabrication and Characterization of Comb-Shaped Lateral Field-Emitter Arrays. Japanese Journal of Applied Physics, 1993, 32, 1221-1226.	0.8	19
119	Low-Operation-Voltage Comb-Shaped Field Emitter Array. Japanese Journal of Applied Physics, 1992, 31, L884-L886.	0.8	9
120	Fabrication and characterization of lateral field-emitter triodes. IEEE Transactions on Electron Devices, 1991, 38, 2334-2336.	1.6	35
121	Silicon films on insulator formation using lateral solid-phase epitaxy induced by focused ion beam. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2699.	1.6	1
122	A novel heteroepitaxy method of Ge films on CaF ₂ by electron beam exposure. Journal of Applied Physics, 1988, 63, 1060-1064.	1.1	27
123	A Novel Electron-Beam Exposure Epitaxy for Growing GaAs Films on Fluoride/Si Structures. Japanese Journal of Applied Physics, 1987, 26, L1834-L1836.	0.8	11
124	Growth and Characterization of Compositionally Graded (Ca, Sr)F ₂ Layers on Si(111) Substrates. Japanese Journal of Applied Physics, 1987, 26, 848-851.	0.8	6
125	Improvement of the quality of Ge films on CaF ₂ /Si(111) structures by predeposited thin Ge layers. Surface Science, 1986, 174, 666-670.	0.8	14
126	Control of Crystal Orientations in Lattice-Mismatched SrF ₂ and (Ca, Sr)F ₂ Films on Si Substrates by Intermediate CaF ₂ Films. Japanese Journal of Applied Physics, 1985, 24, L56-L58.	0.8	12

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127	A MOSFET-structured Si tip for stable emission current. , 0, , .		4
128	Fabrication technology of Si nanodot nanowire memory transistors using an inorganic EB resist process. , 0, , .		1
129	Monolithic integration of Si field emitter arrays with n-MOSFET circuits. , 0, , .		0
130	Silicon nanowire memory using surface charging and its operation analysis by scanning Maxwell-stress microscopy (SMM). , 0, , .		0
131	Electrical and geometrical properties of a Si quantum nanowire device fabricated by an inorganic EB resist process. , 0, , .		0
132	Fabrication of Si FEA integrated with MOSFET driving circuits. , 0, , .		0
133	Modeling of field emission nanotriodes with carbon nanotube emitters. , 0, , .		0
134	Ring-shaped images as a result of non-uniform field emission from capped carbon nanotubes. , 0, , .		0
135	Emission statistics for Si and HfC/Si emitter arrays after gas exposure. , 0, , .		0
136	On the V_{th} controllability for 4-terminal double-gate MOSFETs. , 0, , .		0
137	Demonstration of threshold voltage control techniques for vertical-type 4-terminal double-gate MOSFETs (4T-DGFET). , 0, , .		4
138	STM observations of hafnium carbide thin films as a field emission material. , 0, , .		0
139	Low temperature fabrication of poly-Si FEA for display application. , 0, , .		0
140	Work function control of metal gates by interdiffused Ni-Ta with high thermal stability. , 0, , .		0
141	Focusing Characteristics of Double-Gated Field-Emitter Arrays with a Lower Height of the Focusing Electrode. Applied Physics Express, 0, 1, 053001.	1.1	16